# **Single 2-Input NAND Gate**

The MC74HC1G00 is a high speed CMOS 2–input NAND gate fabricated with silicon gate CMOS technology.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output.

- High Speed:  $t_{PD} = 7 \text{ ns} (Typ)$  at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1 \ \mu A$  (Max) at  $T_A = 25^{\circ}C$
- High Noise Immunity
- Balanced Propagation Delays (t<sub>PLH</sub> = t<sub>PHL</sub>)
- Symmetrical Output Impedance (I<sub>OH</sub> = I<sub>OL</sub> = 2 mA)
- Chip Complexity: FETs = 40
- These Devices are Pb-Free and are RoHS Compliant

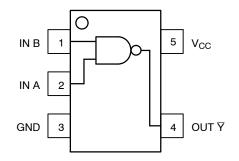


Figure 1. Pinout (Top View)

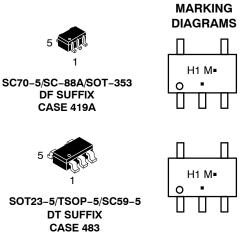


Figure 2. Logic Symbol



# **ON Semiconductor®**

#### http://onsemi.com



H1 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT					
1	IN B				
2	IN A				
3	GND				
4	OUT Y				
5	V <sub>CC</sub>				

#### FUNCTION TABLE

Inp	Inputs				
A	В	Ÿ			
L	L	н			
L	н	Н			
н	L	Н			
Н	Н	L			

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

### MAXIMUM RATINGS

Symbol		Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to V <sub>CC</sub> $+0.5$	V
V <sub>OUT</sub>	DC Output Voltage		$-0.5$ to $V_{CC}$ + 0.5	V
I <sub>IK</sub>	DC Input Diode Current		±20	mA
Ι <sub>ΟΚ</sub>	DC Output Diode Current		±20	mA
I <sub>OUT</sub>	DC Output Sink Current		± 12.5	mA
Icc	DC Supply Current per Supply Pin		±25	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case	e for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias		+ 150	°C
$\theta_{JA}$	Thermal Resistance	SC70-5/SC-88A (Note 1) TSOP-5	350 230	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°	C SC70–5/SC–88A TSOP–5	150 200	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	V
I <sub>LATCHUP</sub>	Latchup Performance	Above $V_{CC}$ and Below GND at 125 $^\circ C$ (Note 5)	$\pm 500$	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace with no air flow.

2. Tested to EIA/JESD22-A114-A.

3. Tested to EIA/JESD22-A115-A.

4. Tested to JESD22-C101-A.

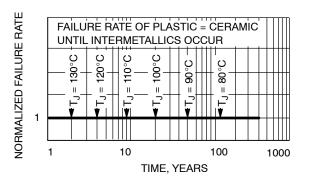
5. Tested to EIA/JESD78.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Мах	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	6.0	V
V <sub>IN</sub>	DC Input Voltage	0.0	V <sub>CC</sub>	V
V <sub>OUT</sub>	DC Output Voltage	0.0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $\begin{array}{c} V_{CC}=2\\ V_{CC}=3\\ V_{CC}=4\\ V_{CC}=6\end{array}$	0 V 0 0 V 0 5 V 0 0 V 0	1000 600 500 400	ns

#### DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0





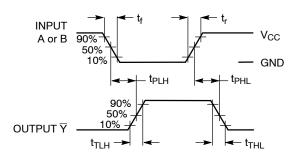
## DC ELECTRICAL CHARACTERISTICS

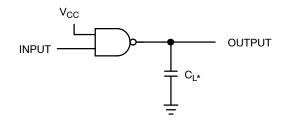
			V <sub>CC</sub>	1	A = 25°C	C	T <sub>A</sub> ≤	85°C	-55°C ≤ 1	Γ <sub>A</sub> ≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High–Level Input Voltage		2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.20			1.5 2.1 3.15 4.20		1.5 2.1 3.15 4.20		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 6.0			0.5 0.9 1.35 1.80		0.5 0.9 1.35 1.80		0.5 0.9 1.35 1.80	V
V <sub>OH</sub>	Minimum High–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		2.0 3.0 4.5 6.0	1.9 2.9 4.4 5.9	2.0 3.0 4.5 6.0		1.9 2.9 4.4 5.9		1.9 2.9 4.4 5.9		V
			4.5 6.0	4.18 5.68	4.31 5.80		4.13 5.63		4.08 5.58		
V <sub>OL</sub>	$\begin{array}{l} \mbox{Maximum Low-Level} \\ \mbox{Output Voltage} \\ \mbox{V}_{IN} = \mbox{V}_{IH} \mbox{ or } \mbox{V}_{IL} \end{array}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 20 \ \mu A$	2.0 3.0 4.5 6.0		0.0 0.0 0.0 0.0	0.1 0.1 0.1 0.1		0.1 0.1 0.1 0.1		0.1 0.1 0.1 0.1	V
			4.5 6.0		0.17 0.18	0.26 0.26		0.33 0.33		0.40 0.40	
I <sub>IN</sub>	Maximum Input Leakage Current	$V_{IN} = 6.0 \text{ V or GND}$	6.0			±0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	6.0			1.0		10		40	μΑ

# **AC ELECTRICAL CHARACTERISTICS** (Input $t_r = t_f = 6.0$ ns)

				Т	A = 25°C	2	T <sub>A</sub> ≤	85°C	-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Test Cond	ditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Maximum	V <sub>CC</sub> = 5.0 V	C <sub>L</sub> = 15 pF		3.5	15		20		25	ns
t <sub>PHL</sub>	Propagation Delay, Input A or B to $\overline{Y}$	$V_{CC} = 2.0 V V_{CC} = 3.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V$	C <sub>L</sub> = 50 pF		19 10.5 7.5 6.5	100 27 20 17		125 35 25 21		155 90 35 26	
t <sub>TLH</sub> ,	Output Transition	V <sub>CC</sub> = 5.0 V	C <sub>L</sub> = 15 pF		3	10		15		20	ns
t <sub>THL</sub>	Time	$V_{CC} = 2.0 V V_{CC} = 3.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V$	C <sub>L</sub> = 50 pF		25 16 11 9	125 35 25 21		155 45 31 26		200 60 38 32	
C <sub>IN</sub>	Maximum Input Capacitance				5	10		10		10	pF
							Туріс	al @ 25°	°C, V <sub>CC</sub> = 5.0	v	
C <sub>PD</sub>	Power Dissipation Ca	pacitance (Note	6)					1	10		pF

6.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no-load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .





\*Includes all probe and jig capacitance. A 1–MHz square input wave is recommended for propagation delay tests.



**DEVICE ORDERING INFORMATION** 

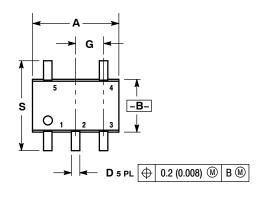
Figure 4. Switching Waveforms

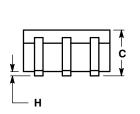
			Device Nom	enclature				
Device Order Number	Logic Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape and Reel Suffix	Package Type	Tape and Reel Size <sup>†</sup>
MC74HC1G00DFT1G	MC	74	HC1G	00	DF	T1	SC70-5/SC-88A/ SOT-353 (Pb-Free)	178 mm (7 in) 3000 Unit
MC74HC1G00DFT2G	MC	74	HC1G	00	DF	T2	SC70-5/SC-88A/ SOT-353 (Pb-Free)	178 mm (7 in) 3000 Unit
MC74HC1G00DTT1G	MC	74	HC1G	00	DT	T1	SOT23-5/TSOP-5/ SC59-5 (Pb-Free)	178 mm (7 in) 3000 Unit

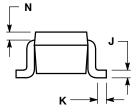
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE K





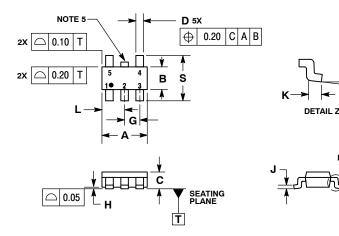


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI V14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02. 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
ſ	0.004	0.010	0.10	0.25
Κ	0.004	0.012	0.10	0.30
Ν	0.008	REF	0.20	REF
s	0.079	0.087	2.00	2.20

#### PACKAGE DIMENSIONS

#### SOT23-5/TSOP-5/SC59-5 DT SUFFIX CASE 483-02 ISSUE H

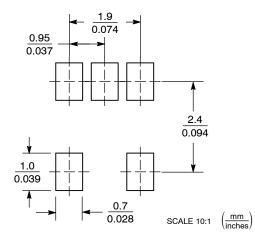


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
- OF BASE MATERIAL. 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
- OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS					
DIM	MIN	MAX				
Α	3.00	BSC				
в	1.50	BSC				
С	0.90	1.10				
D	0.25	0.50				
G	0.95	BSC				
н	0.01	0.10				
J	0.10	0.26				
К	0.20	0.60				
L	1.25	1.25 1.55				
Μ	0 °	0° 10°				
S	2.50	3.00				

#### SOLDERING FOOTPRINT\*



DETAIL Z

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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